

AMENDMENT TO THE SPECIFICATIONS ARE AS FOLLOWS:

The 4th paragraph on page 6 of the application is amended as follows:

The substrate is then subjected to sequential dual annealing steps. The first step is a low energy multiple-pulse laser anneal. Laser parameters are so adjusted as to prevent melting of the amorphized silicon layer by ion implantation during irradiation of the surface. Multiple-pulse laser annealing in the sub-melt regime of the amorphized silicon layer is adequate to activate the dopants and reduce the junction sheet resistance. Due to short annealing time and the absence of melting of the amorphous silicon layer, there is negligible dopant profile widening. Details of laser anneal are: 248 nm wavelength KrF excimer laser, fluence of approximately between about 0.1 and 0.4 J/cm², pulse width of approxi-